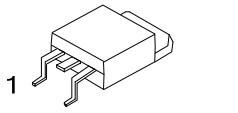
UF540-HC **Preliminary** ***Power MOSFET***

27A, 100V N-CHANNEL POWER MOSFET



TO-252

■ DESCRIPTION

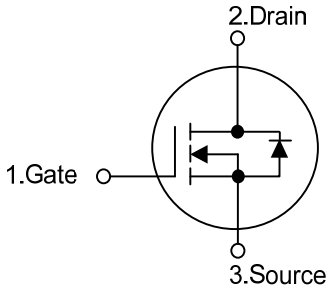
The UTC **UF540-HC** is a N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

The UTC **UF540-HC** is universally applied in low voltage such as automotive, high efficiency switching for AC/DC converters and DC motor control, etc.

■ FEATURES

* $R_{DS(ON)} \leq 48\ m\Omega$ @ V_{GS}=10V, I_D=15A
* High Switching Speed

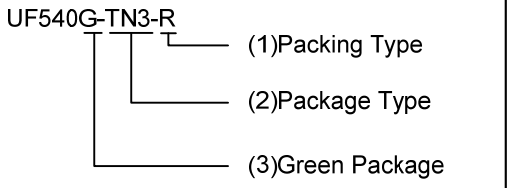
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF540L-TN3-R	UF540G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

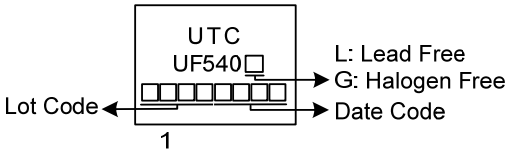


(1) R: Tape Reel

(2) TN3: TO-252

(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	Continuous	I_D	27	A
	Pulsed	I_{DM}	54	A
Single Pulsed Avalanche Current		I_{AS}	6.5	A
Single Pulsed Avalanche Energy		E_{AS}	633	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.8	V/ns
Power Dissipation		P_D	70	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L=30mH, I_{AS}=6.5A, V_{DD}=50V, R_G=25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 27A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	1.78 (Note)	°C/W

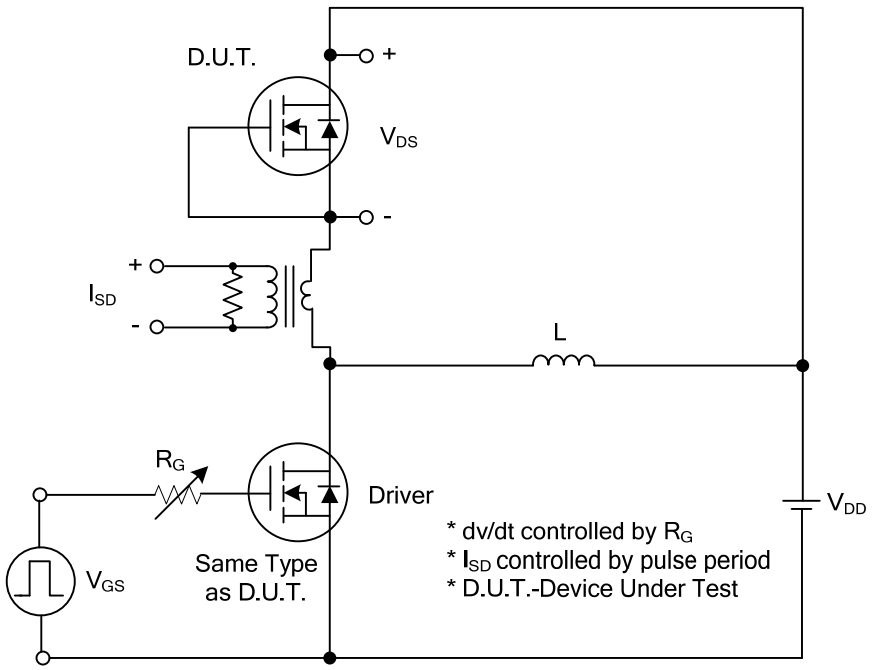
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

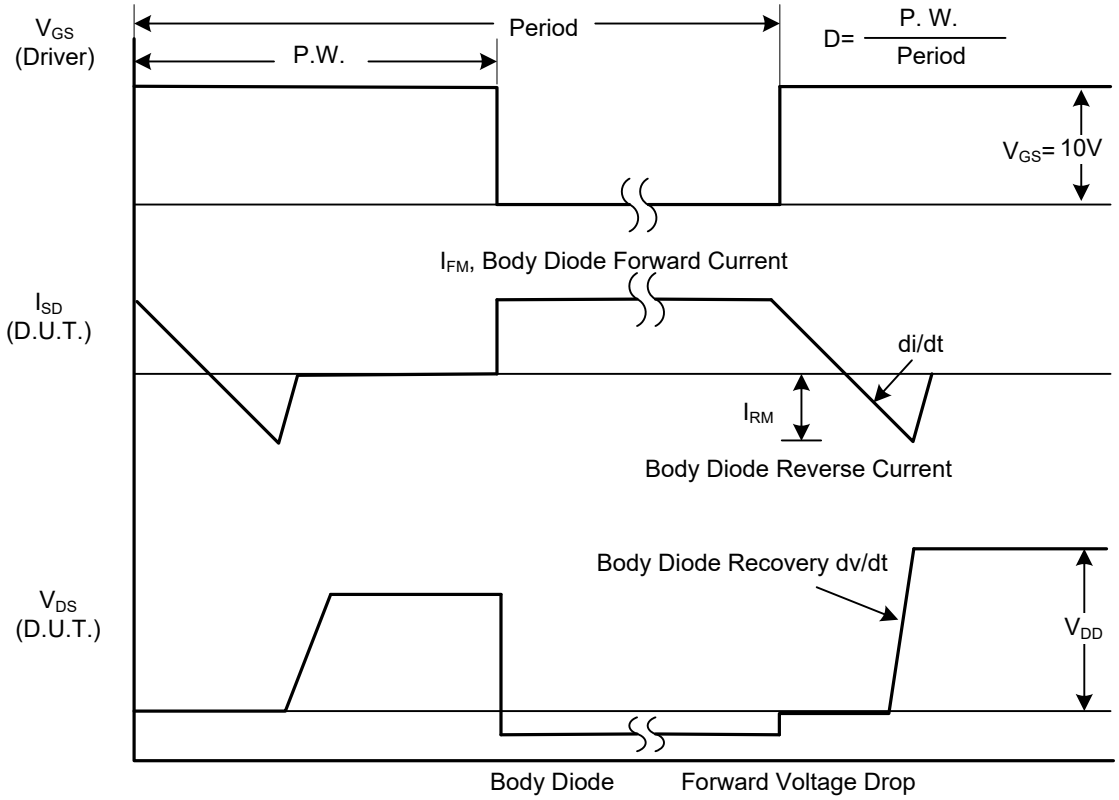
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	100			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=15A			48	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		880		pF
Output Capacitance		C_{OSS}			360		pF
Reverse Transfer Capacitance		C_{RSS}			70		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=80V, V_{GS}=10V, I_D=27A (Note 1, 2)		36		nC
Gate to Source Charge		Q_{GS}			10		nC
Gate to Drain Charge		Q_{GD}			13		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=100V, I_D=27A, R_G=25Ω (Note 1, 2)		10		ns
Rise Time		t_R			24		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			58		ns
Fall-Time		t_F			28		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				27	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				54	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=27A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time		t_{rr}	I_S=27A, V_{GS}=0V, dI_F/dt=100A/μs (Note 1)		66		ns
Reverse Recovery Charge		Q_{rr}			165		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

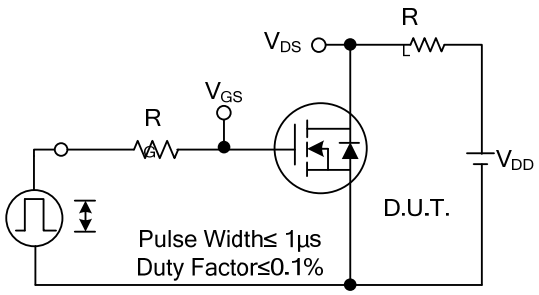


Peak Diode Recovery dv/dt Test Circuit

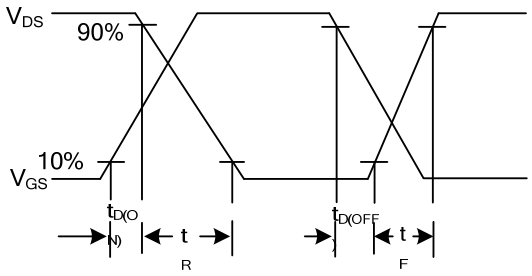


Peak Diode Recovery dv/dt Waveforms

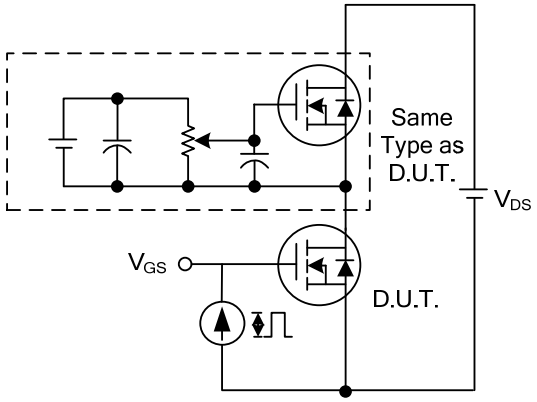
■ TEST CIRCUITS AND WAVEFORMS



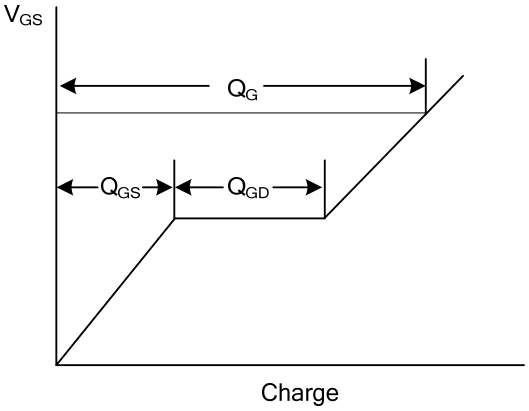
Switching Test Circuit



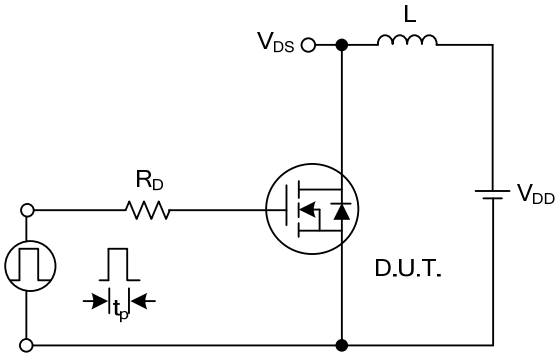
Switching Waveforms



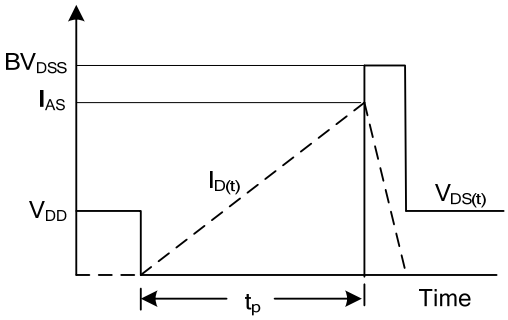
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms